

**AMENDMENTS TO THE CLAIMS**

1. (currently amended) A CMP slurry composition for oxide films comprising:  
  
a solvent;  
  
an abrasive dispersed in the solvent;  
  
an  $\text{HXO}_n$  compound, wherein X is selected from the group consisting of F [, Cl]] and Br and n is an integer ranging from 2 to 4; and  
  
wherein the CMP slurry composition has a pH ranging from 2 to 5 and a polishing selectivity ratio of a nitride film to an oxide film ranging from 1:1 to 1:3.
2. (original) The CMP slurry composition for oxide film according to claim 1, wherein the abrasive is colloidal or fumed  $\text{SiO}_2$  having a grain size of 20 to 300 nm.
3. (original) The CMP slurry composition for oxide film according to claim 1, wherein the abrasive is  $\text{Al}_2\text{O}_3$ .
4. (original) The CMP slurry composition for oxide film according to claim 1, wherein the abrasive is  $\text{CeO}_2$ .
- 5.-7. (canceled)
8. (currently amended) The CMP slurry composition for oxide film according to claim 1, wherein the  $\text{HXO}_n$  compound is ~~selected from the group consisting of  $\text{HClO}_3$ ,  $\text{HClO}_4$ , and  $\text{HBrO}_3$ .~~
9. (Currently amended) The CMP slurry composition for oxide film according to claim 1, wherein the  $\text{HXO}_n$  compound is present in an amount ranging from 0.01 to 10 wt% based on the total amount of the CMP slurry composition.

10. (original) The CMP slurry composition for oxide film according to claim 9, wherein the  $\text{HXO}_n$  compound is present in an amount ranging from 0.1 to 5 wt% based on the CMP slurry.

11. (Canceled)

12. (original) The CMP slurry composition for oxide film according to claim 1, wherein a polishing selectivity ratio of the slurry composition for a nitride film to an oxide film ranges from 1:1 to 1:2.

13.-14. (Canceled)

15. (original) A method for forming a metal line contact plug of a semiconductor device, comprising:

depositing a conductive material for word line on a semiconductor substrate;

forming a word line pattern by depositing a hard mask nitride film on the conductive material for word line;

forming a nitride film spacer at the side of the word line pattern;

forming a planarized interlayer insulating film on the word line pattern;

forming a contact hole by etching the interlayer insulating film until the substrate is exposed;

forming a silicon layer on the entire surface of the interlayer insulating film having the contact hole; and

performing a CMP process on the silicon layer and the interlayer insulating film, by using a CMP slurry composition for oxide film of claim 1 until the hard mask nitride film is exposed.

16. (original) The method according to claim 15, wherein the conductive material for word line is selected from the group consisting of doped silicon, polysilicon, tungsten (W), tungsten nitride (WN), tungsten silicide ( $\text{WSi}_x$ ) and titanium silicide ( $\text{TiSi}_x$ ).

17. (original) The method according to claim 15, wherein the word line pattern is formed by an etching process using  $\text{CCl}_4$  or  $\text{Cl}_2$  gas.

18. (original) The method according to claim 15, wherein the spacer is formed by using TEOS(tetraethoxysilicate glass) or silane( $\text{SiH}_4$ )-base oxide film.

19. (original) The method according to claim 15, wherein the interlayer insulating film is selected from the group consisting of BPSG(borophosphosilicate glass), PSG(phosphosilicate glass), FSG(fluorosilicate glass), PE-TEOS(plasma enhanced tetraethoxysilicate glass), PE- $\text{SiH}_4$ (plasma enhanced-silane), HDP USG(high density plasma undoped silicate glass), HDP PSG(high density plasma phosphosilicate glass) and APL(atomic planarization layer) oxide.

20. (original) The method according to claim 15, wherein the contact hole is formed by an etching process using  $\text{C}_4\text{F}_8$ ,  $\text{C}_2\text{F}_6$  or  $\text{C}_3\text{F}_8$  source.

21. (original) The method according to claim 15, wherein the silicon layer is formed of a doped silicon or polysilicon using  $\text{SiH}_4$  or  $\text{Si}_2\text{H}_6$  source.

22. (original) The method according to claim 15, wherein the CMP process is performed by using a hard pad.

23. (New) The CMP slurry composition according to claim 1, wherein said CMP slurry composition has a polishing selectivity ratio of the a polysilicon layer and an oxide film is 1:1.